

Study on UV FEL single shot damage threshold of an Au thin film

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Depth of crater (nm) 5 5 5 5

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Introduction

We evaluate the damage threshold of an Au coated flat mirror, which is one of the reflective optics installed on FEL-1 beamline of Dalian Coherent Light Source (DCLS), upon far UV free electron laser (FEL) irradiation. The surface of the coating is characterized by profilometer and optical microscope. We present also theoretical approach of the phenomenon by applying single-shot damage threshold calculation, one-dimensional thermal diffusion model as well as finite element analysis with ANSYS to the case.

I. Experimental setup

Subject: Au coated mirror \bullet

200nm Au coating

30nm Cr adhesion layer Si substrate



- Beam size: 0.5 mm in σ of Gaussian
- YAG+CCD measurement with Gaussian fit
- Order of magnitude precision



Wavelength selection: 121.6 nm • Working wavelength of the mirror

III. Result Overview

 Accumulation of crater depth observed 5µJ pulse energy • Still considered single shot (20Hz) A: 2h30min • Threshold is lower than 5µJ pulse B: 10h energy (~2mJ/cm²) Damage of diffraction order observed ___6__ 5µЈ ___6__ 50µЈ ð 50µJ pulse energy A: 5s B: 50s C: 500s D: 30min Irradiated time (s) E: 2h30min

IV. Theoretical approaches



- **Common wavelength for chemical researches in DCLS**
- 20Hz repetition, 2 ps pulse duration, Normal incidence

II. Surface characterization

- An example for 50µJ@2h30min case
- **Optical microscope**
 - Shockwave: typical ultrafast pulse-matter interaction
 - Rise at the center: not the substrate, possible C coated



Profilometer Quantitative depth profile (2 directions) (1.11, 1.15, -8.3)

- Single-shot damage threshold calculation
 - Damage should occur when pulse energy>233 µJ

$$W_{melt} = 3k_B T_{melt}$$
$$W_{atom} = \frac{4ln2(1-R)W_{pulse} msin\theta}{\pi b_{fwhm}^2 d\rho_m}$$

Damage should occur when: $W_{atom} > W_{melt}$

- **One-dimensional thermal diffusion [1]** 2.
 - Simulation indicates that damage should occur for 50µJ pulse energy, but not for 5µJ pulse energy

 $\begin{cases} h_{melt} = C(T)(T - T_0) \\ h_{liquid} = h_{melt} + \Delta h_{latent heat} \end{cases} \quad \frac{\partial h}{\partial t} = \frac{\partial}{\partial x} \left(\frac{K}{C} \frac{\partial h}{\partial x}\right) + S$



3. Finite element analysis of temperature distribution

Simulation indicates that damage should occur for 50µJ pulse energy, but not for 5µJ pulse energy

One-dimensional thermal diffusion simulation







Conclusion

- SSDT is NOT found for Au thin film @121.6nm FEL beam irradiation
 - It should be lower than 5µJ pulse energy (~2mJ/cm²)
 - Further measurements are planned
- Experimental measurements differ from theoretical predictions.
 - SSDT calculation indicates that even 50µJ pulse energy will not cause damage
 - 1D thermal diffusion and FEA indicate that damage should occur for 50µJ case and not for 5µJ case.

[1] Sobierajski, R. et al. Role of Heat Accumulation in the Multi-Shot Damage of Silicon Irradiated with Femtosecond XUV Pulses at a 1 MHz Repetition Rate. Opt. Express 2016, 24 (14), 15468. https://doi.org/10.1364/OE.24.015468.

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